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Manufacturing of void-filled Cu samples for breakdown experiments in the DC spark setup

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Motivation

Simulation work (Aarne Pohjonen, Stefan Parviainen) suggests that voids under the surface of the cathode are a significant cause of breakdown

This result can be tested empirically in the DC spark setup if we have samples with voids

We are manufacturing samples in Helsinki:

- He ions implanted into the sample by irradiation (done!)
- He is nucleated into bubbles and then removed through annealing, leaving behind voids
- The successful creation of voids is confirmed through positron annihilation spectroscopy

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Irradiation

Relationship between implantation depth and ion energy was studied with SRIM:



SRIM simulation of He ion implantation into Cu sample, ion energy of 30 keV

Irradiation of samples was conducted using ion energy of 30 keV, dose chosen to yield 5 at% He at most common stopping range

Each of the 12 samples had half of it masked with aluminium tape to provide a control sample



Annealing (planned)

Implanted He tends to form small (<10 atoms) clusters around metal lattice vacancies

Significant diffusion needed to make He nucleate into bubbles, as well as leave sample

Annealing likely needed

Plan: Leave 4 samples un-annealed, anneal the rest using lowest reasonable temperature (to prevent blistering)

Use positron annihilation spectroscopy to verify successful manufacture of voids

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